



GL25N06B3

无锡光磊电子科技有限公司

GL Silicon N-Channel Power MOSFET

General Description

The GL25N06B3 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications. The package form is TO-251, which accords with the RoHS standard.

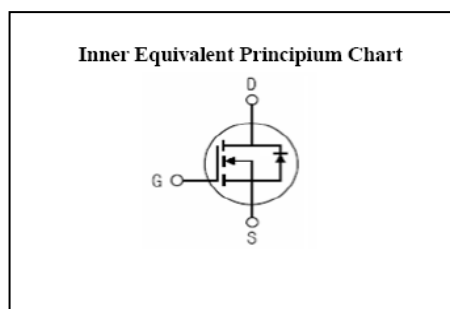
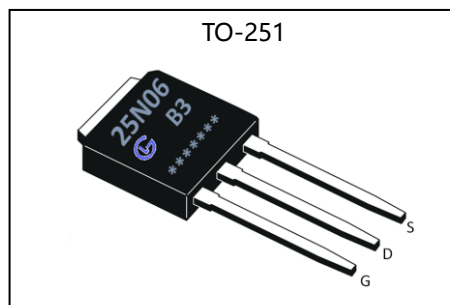
V _{DSS}	60	V
I _D	25	A
P _D	50	W
R _{DS(ON)TYP}	25	mΩ

Features

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Absolute (T_c= 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DSS}	Drain-to-Source Voltage	60	V
I _D	Continuous Drain Current	25	A
	Continuous Drain Current T _C = 100 °C	18	A
I _{DM}	Pulsed Drain Current	80	A
V _{GS}	Gate-to-Source Voltage	±20	V
E _{AS} ^{a2}	Single Pulse Avalanche Energy	72	mJ
E _{AR} ^{a1}	Avalanche Energy ,Repetitive	18	mJ
I _{AR} ^{a1}	Avalanche Current	11	A
dv/dt ^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P _D	Power Dissipation	50	W
T _J , T _{stg}	Operating Junction and Storage Temperature Range	175, -55 to 175	°C
T _L	Maximum Temperature for Soldering	300	°C

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device

**GL Silicon N-Channel Power MOSFET****Electrical Characteristics** (Tc=25°C unless otherwise specified)

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu A$, Reference 25°C	--	0.05	--	V/°C
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=60V, V_{GS}=0V, T_a=25^\circ C$	--	--	1	μA
		$V_{DS}=48V, V_{GS}=0V, T_a=125^\circ C$	--	--	250	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V$	--	--	1	μA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V$	--	--	-1	μA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=20A$	--	25	30	m Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	--	3.0	V
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=5A$	11	--	--	S
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=30V$ $f=1.0MHz$	--	500	--	pF
C_{oss}	Output Capacitance		--	60	--	
C_{rss}	Reverse Transfer Capacitance		--	25	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=2A, V_{DD}=30V$ $V_{GS}=10V, R_G=3.0\Omega$	--	6	--	ns
t_r	Rise Time		--	2.8	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	9	--	
t_f	Fall Time		--	5.0	--	
Q_g	Total Gate Charge	$I_D=4.5A, V_{DD}=30V$ $V_{GS}=10V$	--	11	--	nC
Q_{gs}	Gate to Source Charge		--	6	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	3	--	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	25	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	80	A
V_{SD}	Diode Forward Voltage	$I_S=25A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=25A, T_J=25^\circ C$	--	35	--	ns
Q_{rr}	Reverse Recovery Charge	$dI_F/dt=100A/us, V_{GS}=0V$	--	50	--	nC

Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$

Thermal Characteristics

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	3.0	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: EAS condition : $T_J=25^\circ C$, $V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$

^{a3}: $I_{SD}=10A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}$, Start $T_J=25^\circ C$

Test Circuits

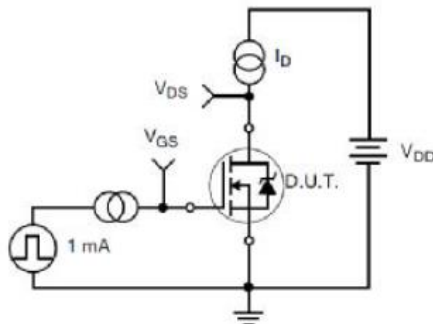


Figure 17. Gate Charge Test Circuit

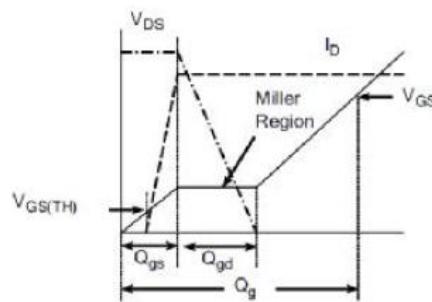


Figure 18. Gate Charge Waveform

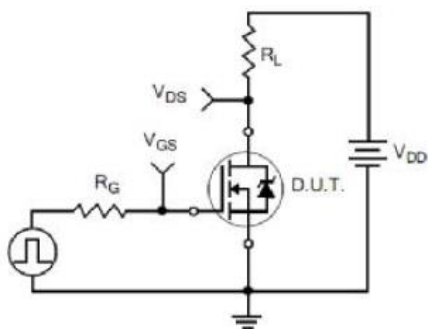


Figure 19. Resistive Switching Test Circuit

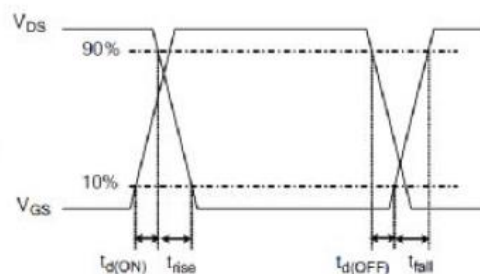
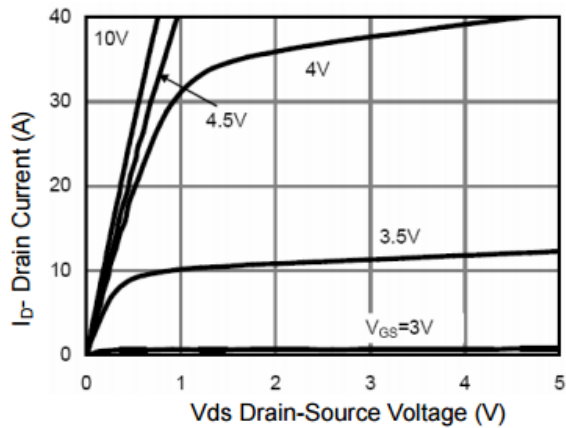
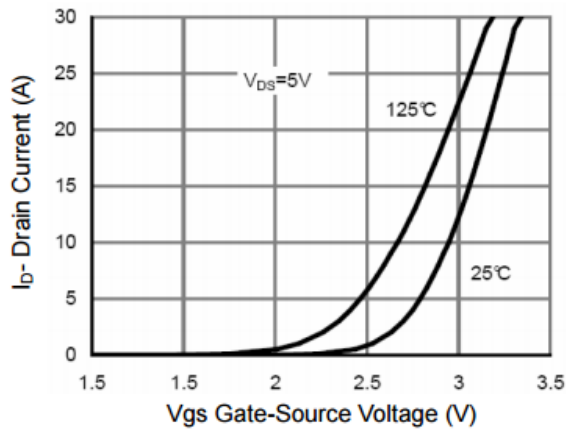
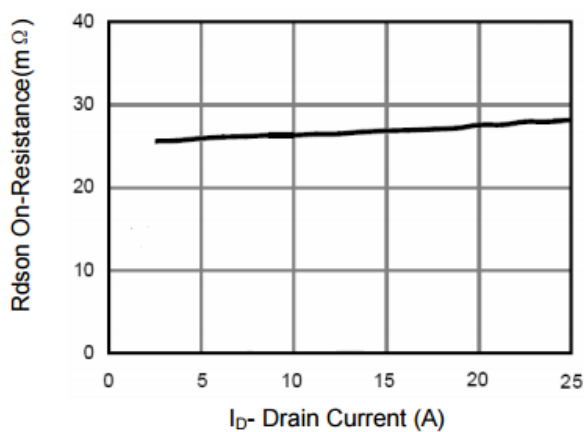
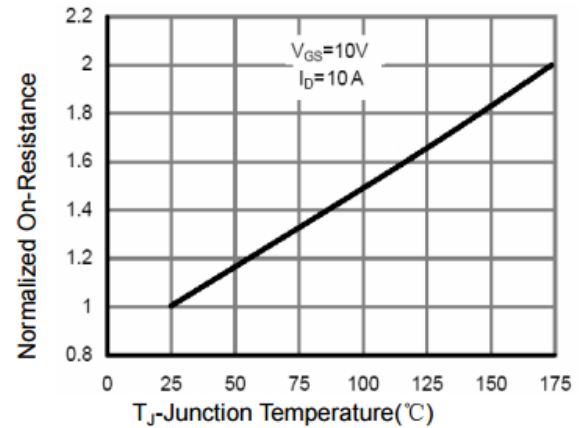
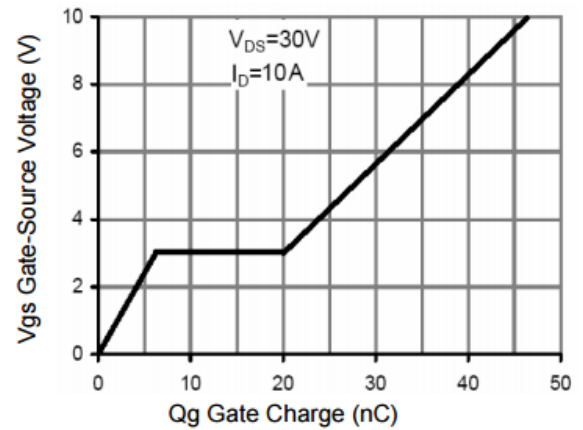
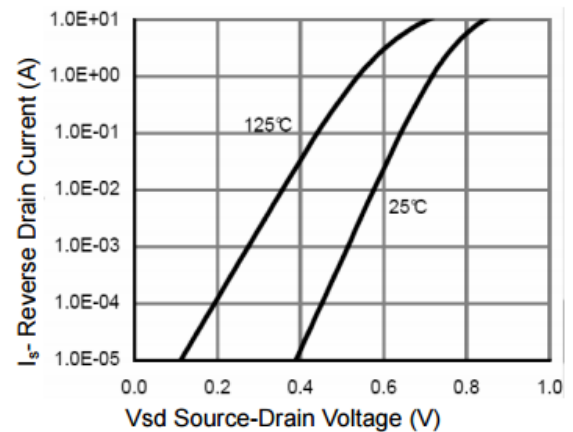


Figure 20. Resistive Switching Waveforms

Characteristics Curves

Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 Rdson- Drain Current

Figure 4 Rdson-Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward

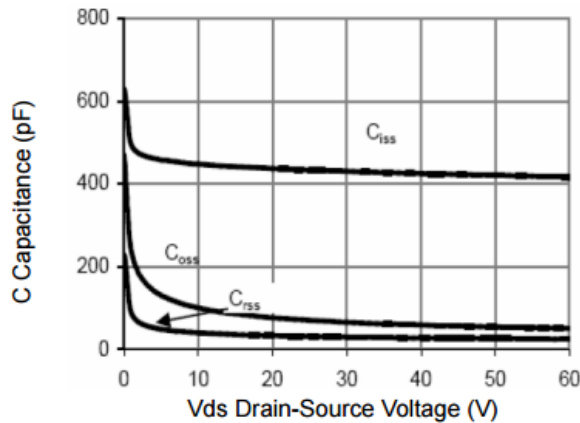


Figure 7 Capacitance vs Vds

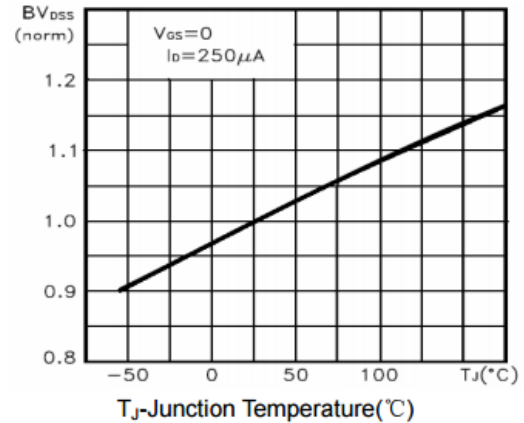


Figure 9 BV_{DSS} vs Junction Temperature

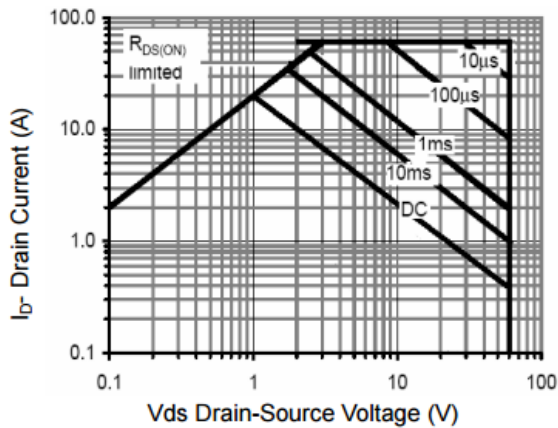


Figure 8 Safe Operation Area

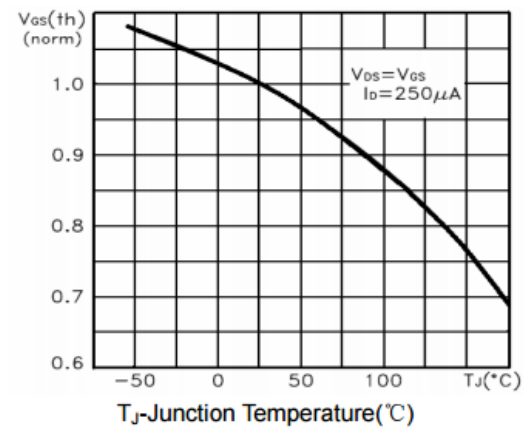


Figure 10 $V_{GS(th)}$ vs Junction Temperature

